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Kind regards,

Team Nexperia

NPN/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

Rev. 01 — 31 March 2006

Product data sheet

1. Product profile

1.1 General description

NPN/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	ber Package		PNP/PNP	NPN/NPN	
	Philips	JEITA	complement	complement	
PEMD30	SOT666	-	PEMB30	PEMH30	
PUMD30	SOT363	SC-88	PUMB30	PUMH30	

Reduces pick and place costs

and BC847BVN

Switching loads

Cost-saving alternative for BC847BPN

1.2 Features

- 100 mA output current capability
 Reduces component count
- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- 1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor; for the PNP transistor	with negative pol	arity			
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ



006aaa269

NPN/PNP double resistor-equipped transistors; R1 = 2.2 kΩ, R2 = open

2. Pinning information

Table 3.	Pinning			
Pin	Description	Simplified outline	Symbol	
1	GND (emitter) TR1			
2	input (base) TR1	6 5 4		
3	output (collector) TR2			
4	GND (emitter) TR2			
5	input (base) TR2			
6	output (collector) TR1	001aab555	R1	
			1 2 3	

3. Ordering information

Table 4.Ordering information

Type number	Package	ickage				
	Name	Description	Version			
PEMD30	-	plastic surface-mounted package; 6 leads	SOT666			
PUMD30	SC-88	plastic surface-mounted package; 6 leads	SOT363			

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PEMD30	2U
PUMD30	*B3

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

NPN/PNP double resistor-equipped transistors; R1 = 2.2 kΩ, R2 = open

5. Limiting values

Symbol	Parameter	Conditions		Min	Max	Unit
Per transi	stor; for the PNP transistor	with negative pol	arity			
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
lo	output current			-	100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u>	-	200	mW
	SOT666		[1][2]	-	200	mW
Per device)					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C				
	SOT363		<u>[1]</u>	-	300	mW
	SOT666		[1][2]	-	300	mW
T _{stg}	storage temperature			-65	+150	°C
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		[1][2] _	-	625	K/W
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1][2] _	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

NPN/PNP double resistor-equipped transistors; R1 = 2.2 kΩ, R2 = open

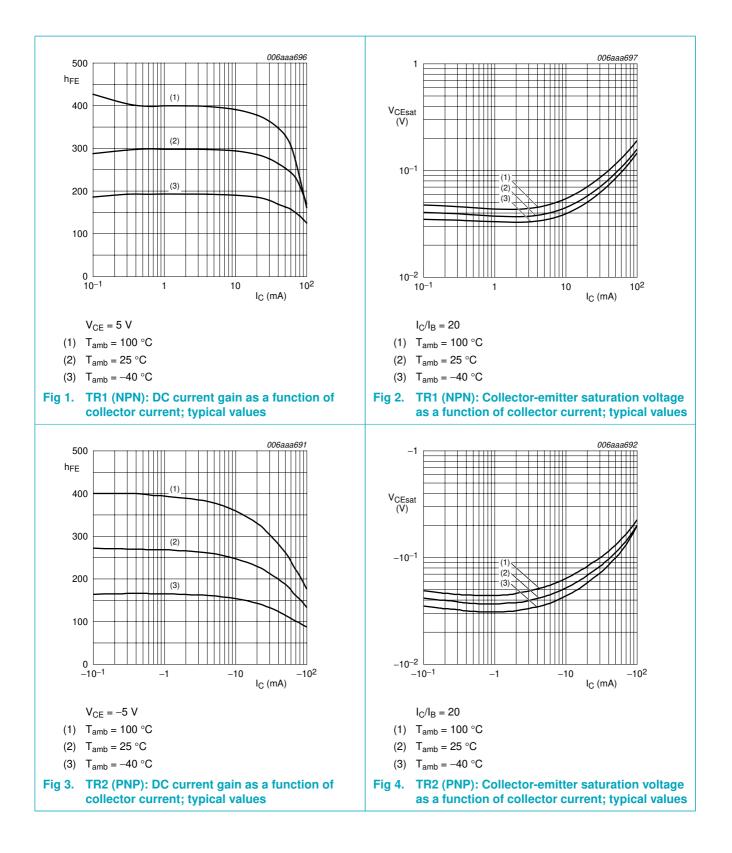
7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor; for the PNP transi	stor with negative polarity				
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	CEO collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$	-	-	1	μA
	current	$\label{eq:Vce} \begin{split} V_{CE} &= 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \\ T_{j} &= 150 ^{\circ}\text{C} \end{split}$	-	-	50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 20 \text{ mA}$	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = 10 \text{ mA}; I_{B} = 0.5 \text{ mA}$	-	-	150	mV
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	рF

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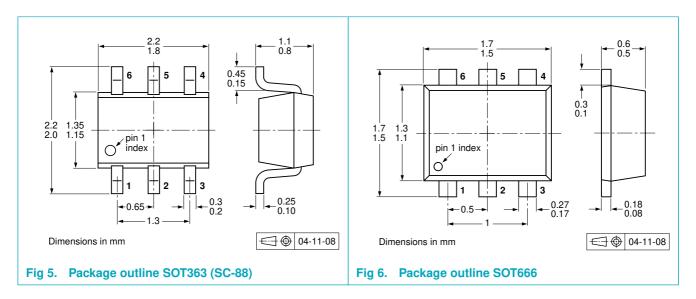
PEMD30; PUMD30

NPN/PNP double resistor-equipped transistors; R1 = 2.2 kΩ, R2 = open



NPN/PNP double resistor-equipped transistors; R1 = 2.2 kΩ, R2 = open

8. Package outline



9. Packing information

Table 9.Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packi	ng quar	ntity	
				4000	8000	10000
PEMD30	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMD30 SOT363		4 mm pitch, 8 mm tape and reel; T1	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165

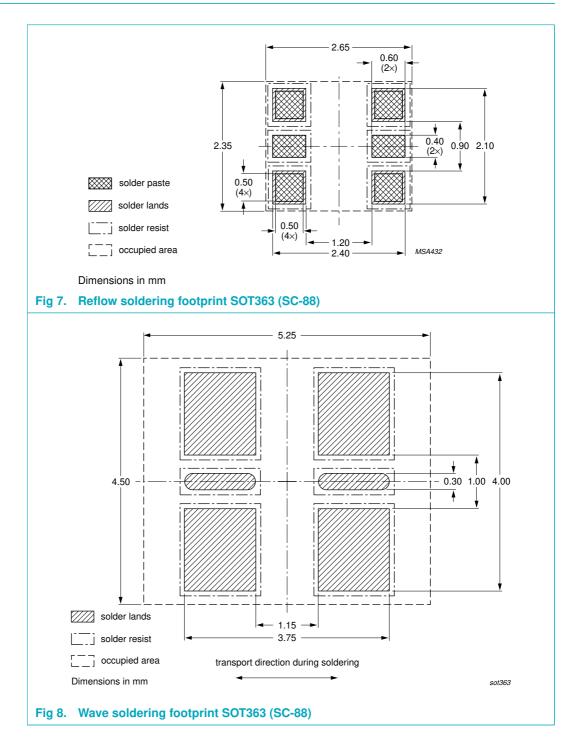
[1] For further information and the availability of packing methods, see Section 13.

[2] T1: normal taping

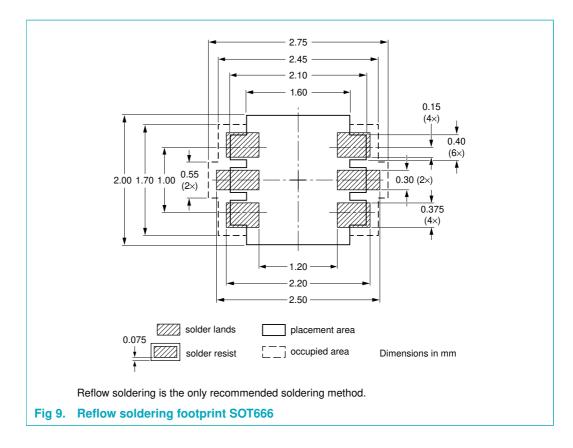
[3] T2: reverse taping

NPN/PNP double resistor-equipped transistors; R1 = 2.2 kΩ, R2 = open

10. Soldering



NPN/PNP double resistor-equipped transistors; R1 = 2.2 kΩ, R2 = open



NPN/PNP double resistor-equipped transistors; R1 = 2.2 kΩ, R2 = open

11. Revision history

Table 10. Revision hist	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PEMD30_PUMD30_1	20060331	Product data sheet	-	-			

NPN/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PEMD30; PUMD30

NPN/PNP double resistor-equipped transistors; R1 = 2.2 kΩ, R2 = open

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